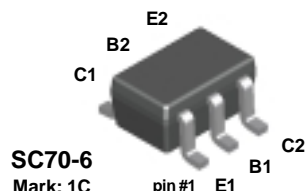


# BC847S



NOTE: The pinouts are symmetrical; pin 1 and pin 4 are interchangeable. Units inside the carrier can be of either orientation and will not affect the functionality of the device.

## NPN Multi-Chip General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 200 mA. Sourced from Process 07.

### Absolute Maximum Ratings\*

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	45	V
$V_{CES}$	Collector-Base Voltage	50	V
$V_{CBO}$	Collector-Base Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	6.0	V
$I_C$	Collector Current - Continuous	200	mA
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Characteristic	Max	Units
		BC847S	
$P_D$	Total Device Dissipation Derate above $25^\circ\text{C}$	300 2.4	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	$^\circ\text{C/W}$

NPN Multi-Chip General Purpose Amplifier  
(continued)

Electrical Characteristics  $T_A = 25^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{ mA}, I_B = 0$	45			V
$V_{(BR)CES}$	Collector-Base Breakdown Voltage	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	6.0			V
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = 30\text{ V}, I_E = 0$ $V_{CB} = 30\text{ V}, I_E = 0, T_A = 150^{\circ}\text{C}$			15 5.0	nA $\mu\text{A}$

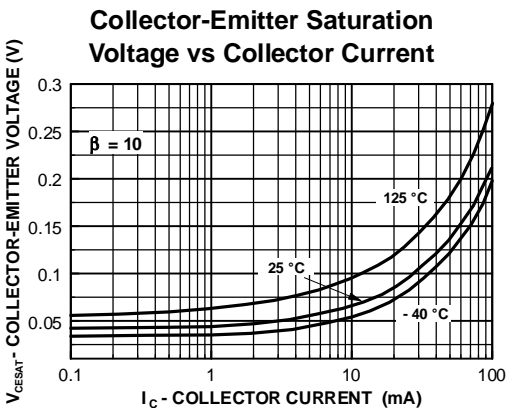
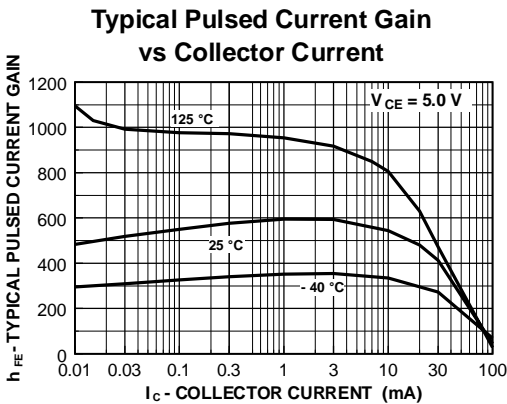
ON CHARACTERISTICS

$h_{FE}$	DC Current Gain	$I_C = 2.0\text{ mA}, V_{CE} = 5.0\text{ V}$	110		630	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}, I_B = 5.0\text{ mA}$			0.25 0.65	V V
$V_{BE(on)}$	Base-Emitter ON Voltage	$I_C = 2.0\text{ mA}, V_{CE} = 5.0\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 5.0\text{ V}$	0.58		0.7 0.77	V V

SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 20\text{ mA}, V_{CE} = 5.0,$ $f = 100\text{ mHz}$		200		MHz
$C_{obo}$	Output Capacitance	$V_{CB} = 10\text{ V}, f = 1.0\text{ MHz}$		2.0		pF

Typical Characteristics

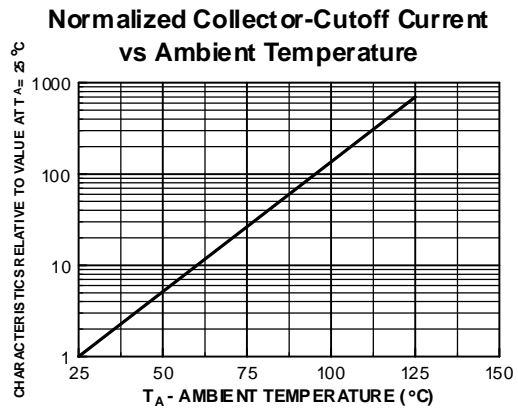
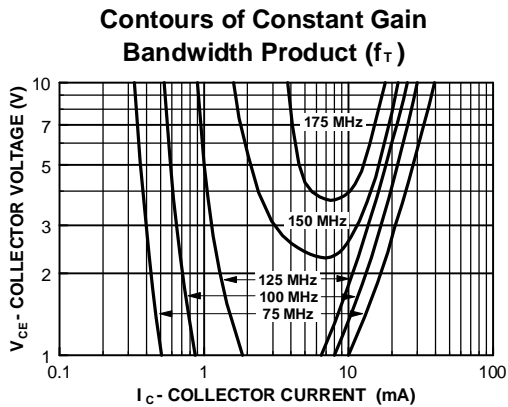
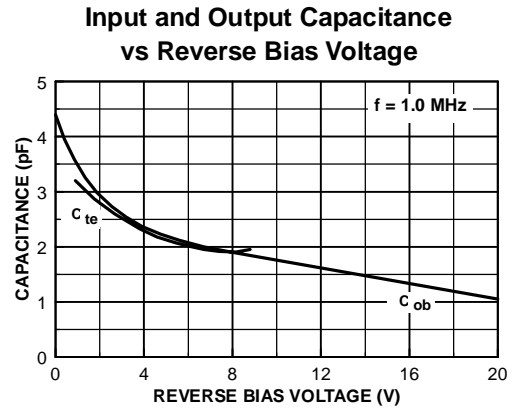
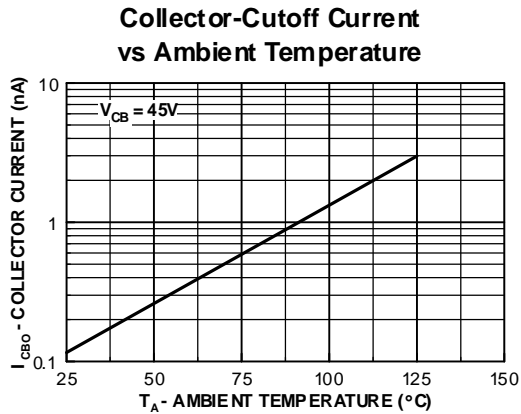
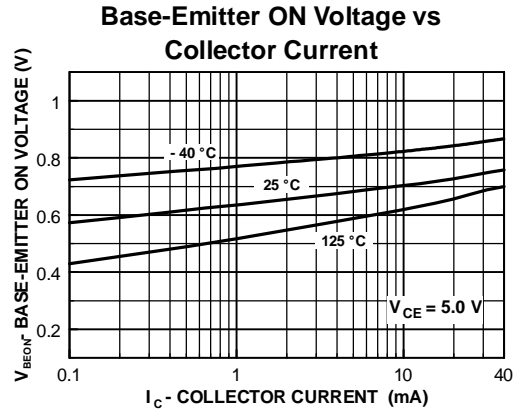
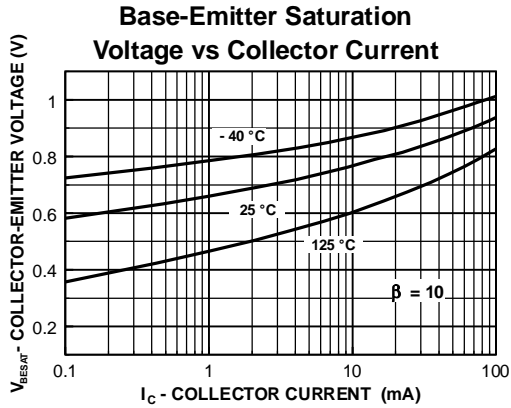


# NPN Multi-Chip General Purpose Amplifier

(continued)

BC847S

## Typical Characteristics

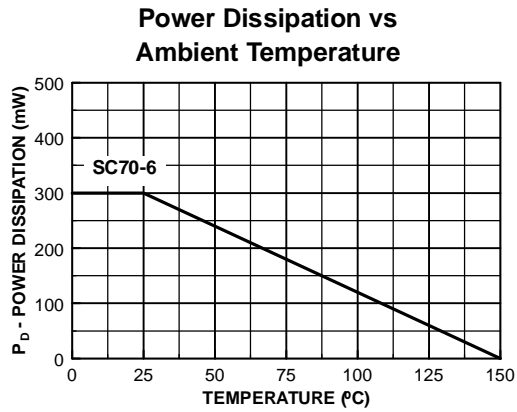
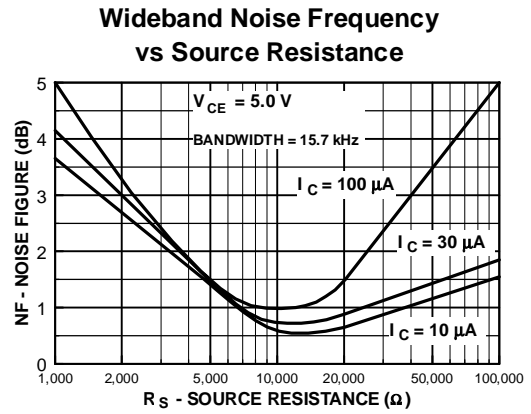
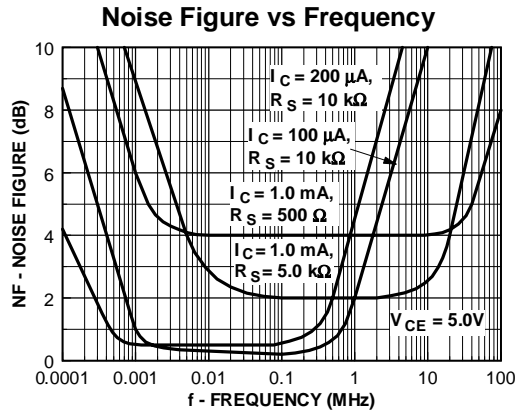


# NPN Multi-Chip General Purpose Amplifier

(continued)

BC847S

## Typical Characteristics (continued)



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